IN THE UNITED STATES PATENT AND TRADEMARK OFFIC

| Priority Application Serial No |
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| <u>Priority</u> Filing Date |
| Inventor Schuegraf |
| Assignee Micron Technology, Inc. |
| Priority Group Art Unit |
| Priority Examiner M. Whipple |
| Attorney's Docket No |
| Title: Semiconductor Processing Methods of Chemical Vapor Depositing SiO ₂ on a Substrate |

PRELIMINARY AMENDMENT

To:

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Box PATENT APPLICATION

Assistant Commissioner for Patents

Washington, D.C. 20231

From:

Lance R. Sadler (Tel. 509-624-4276; Fax 509-838-3424)

Wells, St. John, Roberts, Gregory & Matkin P.S.

601 W. First Avenue, Suite 1300 Spokane, WA 99201-3817

Sir:

Applicant preliminarily amends as follows:

<u>AMENDMENTS</u>

In the Specification

On page 1, before the "Technical Field" section, insert the following section:

--RELATED PATENT DATA

This patent resulted from a continuation application of U.S. Patent Application Serial No. 08/696,243, filed August 13, 1996, entitled "Semiconductor Processing Methods of Chemical Vapor Depositing SiO₂

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